

# PSMN1R1-30EL

N-channel 30 V 1.3 mΩ logic level MOSFET in I2PAK

2 April 2014 Product data sheet

### 1. General description

Logic level N-channel MOSFET in I2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

### 3. Applications

- DC-to-DC converters
- Load switiching
- Motor control
- Server power supplies

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	30	V	
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 2</u>	[1]	-	-	120	Α	
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	338	W	
T <sub>j</sub>	junction temperature			-55	-	175	°C	
Static characte	Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 12	[2]	-	1.1	1.3	mΩ	
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; Fig. 13		-	1.5	1.8	mΩ	
Dynamic chara	acteristics						,	
$Q_{GD}$	gate-drain charge	$V_{GS}$ = 4.5 V; $I_D$ = 75 A; $V_{DS}$ = 15 V;		-	37	-	nC	
Q <sub>G(tot)</sub>	total gate charge	<u>Fig. 14; Fig. 15</u>		-	118	-	nC	



#### N-channel 30 V 1.3 m $\Omega$ logic level MOSFET in I2PAK

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Avalanche rug	Avalanche ruggedness							
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 120 A; $V_{sup} \le$ 30 V; $R_{GS}$ = 50 Ω; unclamped		-	-	1.9	J	

- Continuous current is limited by package. Measured 3 mm from package.

# **Pinning information**

Table 2. **Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D I
2	D	drain		
3	S	source		G—UNA)
mb	D	mounting base; connected to drain		mbb076 S
			I2PAK (SOT226)	

## **Ordering information**

Table 3. **Ordering information** 

Type number	Package					
	Name	Description	Version			
PSMN1R1-30EL	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226			

# **Marking**

Table 4. **Marking codes** 

Type number	Marking code
PSMN1R1-30EL	PSMN1R1-30EL

#### **Limiting values** 8.

#### **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	30	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	30	V
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Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>GS</sub>	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	338	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>	[1]	-	120	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	120	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 ^{\circ}C$ ; Fig. 3		-	1609	Α
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-dra	in diode					
Is	source current	T <sub>mb</sub> = 25 °C	[1]	-	120	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	1609	Α
Avalanche	ruggedness	1	1	1	1	
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 120 A; $V_{sup} \le$ 30 V; $R_{GS}$ = 50 Ω; unclamped		-	1.9	J

#### [1] Continuous current is limited by package.

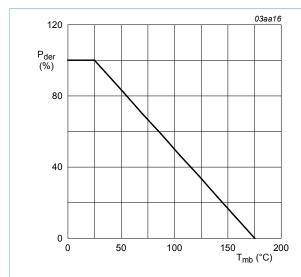


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{\textit{der}} = \frac{P_{\textit{tot}}}{P_{\textit{tot}(25^{\circ}\text{C})}} \times \textbf{100 \%}$$

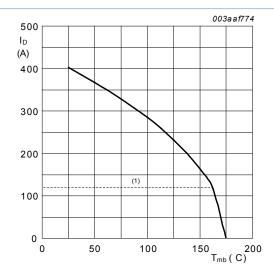


Fig. 2. Continuous drain current as a function of mounting base temperature.

 $V_{\it GS} \! \geq 10 \; {
m V}; \;\;$  (1) Capped at 120 A due to package

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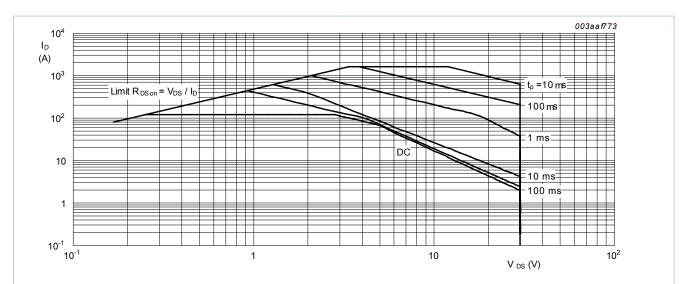


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb}$  = 25 °C;  $I_{DM}$  is a single pulse; Capped at 120 A due to package

#### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	0.22	0.44	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W

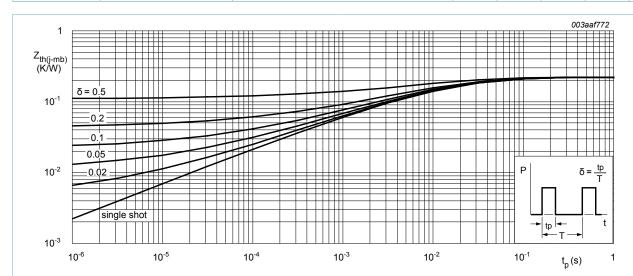


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

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### 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Uni
Static chara	cteristics						
V <sub>(BR)DSS</sub> drain-source		I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		30	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C		27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; Fig. 10; Fig. 11		1.3	1.7	2.15	V
		$I_D$ = 2 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; Fig. 11		0.5	-	-	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; Fig. 11		-	-	2.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	0.02	10	μΑ
		V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C		-	250	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	10	100	nA
		V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 12	[1]	-	1.1	1.3	mΩ
		$V_{GS}$ = 4.5 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 12		-	1.2	1.6	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 175 °C; Fig. 13; Fig. 12		-	2.1	2.5	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 100 °C; Fig. 13		-	1.5	1.8	mΩ
$R_G$	gate resistance	f = 1 MHz		-	1.1	-	Ω
Dynamic cha	aracteristics						
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 75 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15		-	243	-	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15		-	222	-	nC
		I <sub>D</sub> = 75 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V;		-	118	-	nC
$Q_{GS}$	gate-source charge	Fig. 14; Fig. 15		-	39	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge			-	22	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge			-	17	-	nC
$Q_{GD}$	gate-drain charge			-	37	-	nC
V <sub>GS(pI)</sub>	gate-source plateau voltage	V <sub>DS</sub> = 15 V; <u>Fig. 14</u> ; <u>Fig. 15</u>		-	2.8	-	V

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#### N-channel 30 V 1.3 m $\Omega$ logic level MOSFET in I2PAK

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$		-	14850	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 16</u>		-	2799	-	pF
C <sub>rss</sub>	reverse transfer capacitance			-	1215	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; $R_{L}$ = 0.2 $\Omega$ ; $V_{GS}$ = 4.5 V; $R_{G(ext)}$ = 5 $\Omega$ ; $I_{D}$ = 75 A; $T_{j}$ = 25 °C		-	95	-	ns
t <sub>r</sub>	rise time			-	213	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	199	-	ns
t <sub>f</sub>	fall time			-	115	-	ns
Source-dra	ain diode		l				
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$		-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$ $V_{DS} = 15 \text{ V}$		-	67	-	ns
Q <sub>r</sub>	recovered charge			-	123	-	nC

#### [1] Measured 3 mm from package.

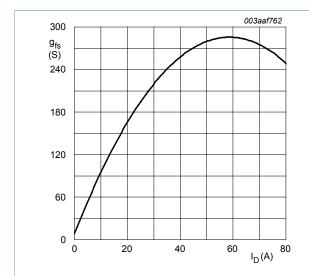


Fig. 5. Forward transconductance as a function of drain current; typical values

$$T_j=25\,^{\circ}C; V_{DS}=15\,V$$

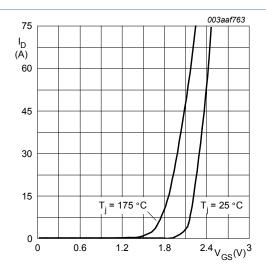


Fig. 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} > I_D \times R_{DSon}$$

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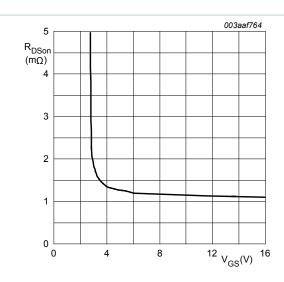


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25 \,^{\circ}C; I_D = 25A$$

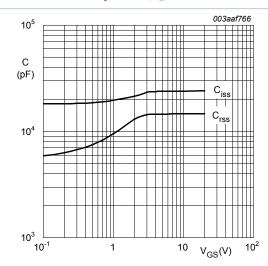


Fig. 9. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

$$V_{DS} = 0V; f = 1MHz$$

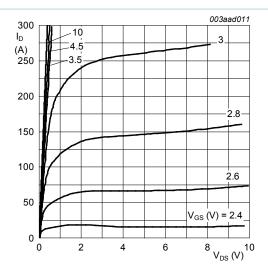


Fig. 8. Output characteristics: drain current as a function of drain-source voltage; typical values

$$T_j = 25\,^{\circ}C$$

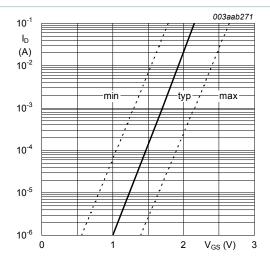


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25 \,^{\circ}C; V_{DS} = 5V$$

#### N-channel 30 V 1.3 m $\Omega$ logic level MOSFET in I2PAK

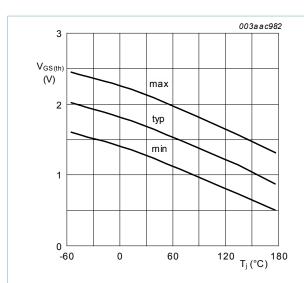


Fig. 11. Gate-source threshold voltage as a function of junction temperature

 $I_D = 1mA; V_{DS} = V_{GS}$ 

2

1.5

0.5

0

-60

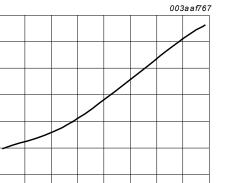


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

0

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

60

120 <sub>T<sub>j</sub></sub> (C) 180

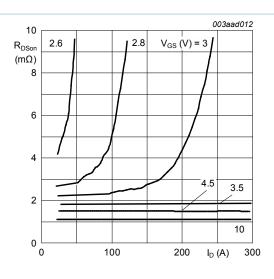


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

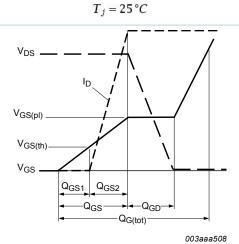


Fig. 14. Gate charge waveform definitions

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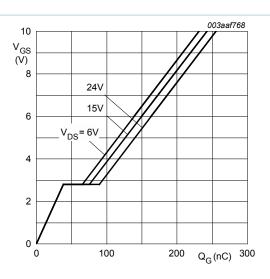


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
 °C;  $I_D = 75$  A

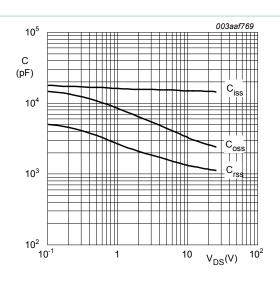


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

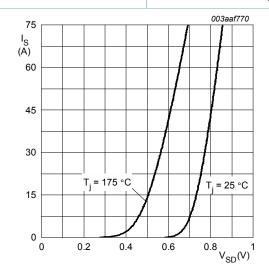


Fig. 17. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0 V$$

# 11. Package outline

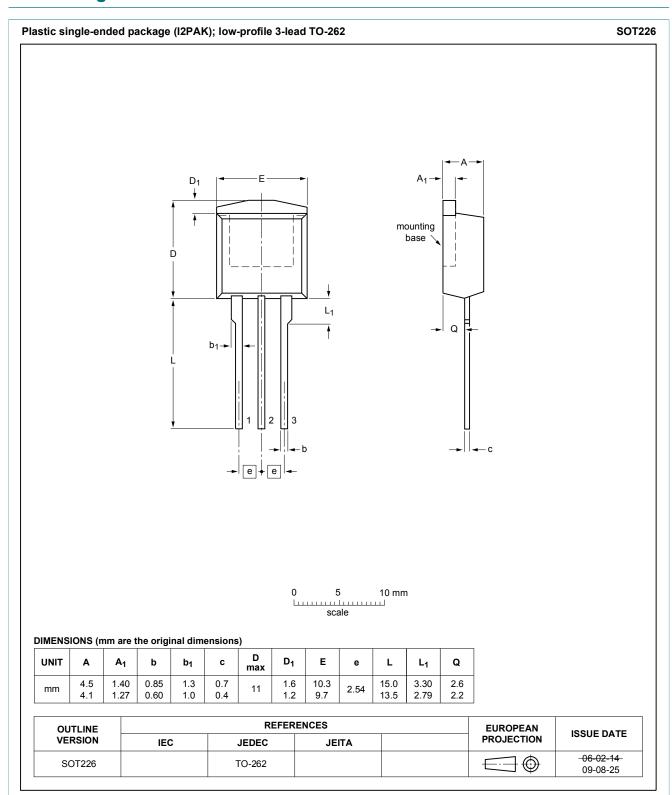


Fig. 18. Package outline I2PAK (SOT226)

### N-channel 30 V 1.3 mΩ logic level MOSFET in I2PAK

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#### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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TPCC8103,L1Q(CM MIC4420CM-TR VN1206L 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C

IPS70R2K0CEAKMA1 BUK954R8-60E DMN3404LQ-7 NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI

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